

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07384

DT-33-19

2SB995

SILICON PNP TRIPLE DIFFUSED TYPE

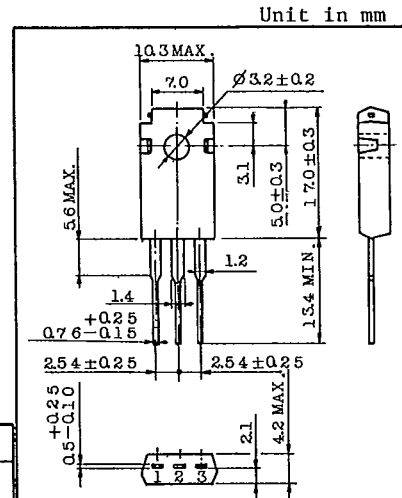
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- High Breakdown Voltage : $V_{CE0} = -100V$
- Low Collector-Emitter Saturation Voltage
: $V_{CE(sat)} = -2.0V(\text{Max.})$
- Complementary to 2SD1355
- Recommended for 30W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-100	V
Collector-Emitter Voltage	V_{CE0}	-100	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-5	A
Base Current	I_B	-0.5	A
Collector Power Dissipation ($T_c = 25^\circ C$)	P_C	40	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC

EIAJ

TOSHIBA 2-10K1A

Weight : 2.0g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB} = -100V, I_E = 0$	-	-	-100	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = -5V, I_C = 0$	-	-	-1	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_C = -50mA, I_B = 0$	-100	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -5V, I_C = -1A$	40	-	240	
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -4A$	20	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -4A, I_B = -0.4A$	-	-	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -4A$	-	-	-1.5	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -1A$	-	5	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	270	-	pF

Note : $h_{FE(1)}$ Classification R : 40 ~ 80, O : 70 ~ 140, Y : 120 ~ 240

TOSHIBA CORPORATION

